# 2SK3539G

## Silicon N-channel MOSFET

### For switching

#### ■ Features

- High-speed switching
- Wide frequency band
- Gate protection diode built-in

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source voltage	V <sub>DS</sub>	50	V	
Gate-source voltage (Drain open)	$V_{GSO}$	±7	V	
Drain current	$I_D$	100	mA	
Peak drain current	$I_{DP}$	200	mA	
Power dissipation	$P_{\mathrm{D}}$	150	mW	
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

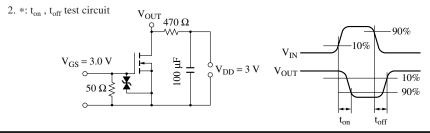
#### ■ Package

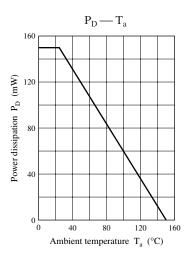
- Code
  - SMini3-F2
- Marking Symbol: 5F
- Pin Name
  - 1: Gate
  - 2: Source
  - 3: Drain

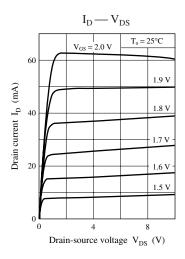
## ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

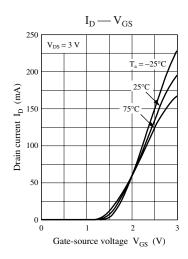
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	$V_{\rm DSS}$	$I_D = 10 \ \mu A, \ V_{GS} = 0$	50			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = 50 \text{ V}, V_{GS} = 0$			1.0	μΑ
Gate-Source cutoff current	$I_{GSS}$	$V_{GS} = \pm 7 \text{ V}, V_{DS} = 0$			±5.0	μΑ
Gate threshold voltage	$V_{th}$	$I_D = 1.0 \ \mu A, \ V_{DS} = 3 \ V$	0.9	1.2	1.5	V
Drain-source ON resistance	R <sub>DS(on)</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		8	15	Ω
		$I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$		6	12	
Forward transfer admitance	$ Y_{fs} $	$I_D = 10 \text{ mA}, V_{DS} = 3 \text{ V}, f = 1 \text{ kHz}$	20	60		mS
Short-circuit forward transfer capacitance (Common source)	C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		12		pF
Short-circuit output capacitance (Common source)	C <sub>oss</sub>			7		pF
Reverse transfer capacitance (Common source)	C <sub>rss</sub>			3		pF
Turn-on time *	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, V_{GS} = 0 \text{ V to } 3 \text{ V}, R_L = 470 \Omega$		200		ns
Turn-off time *	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, V_{GS} = 3 \text{ V to } 0 \text{ V}, R_{L} = 470 \Omega$		200		ns

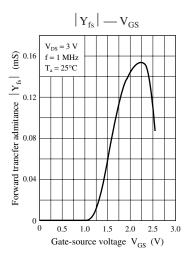
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

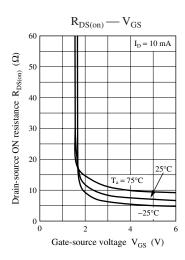


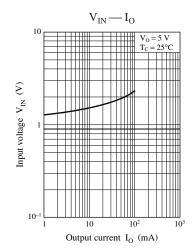






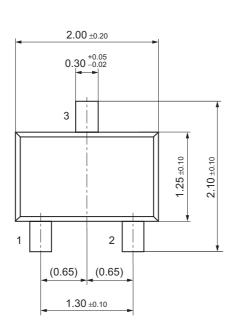


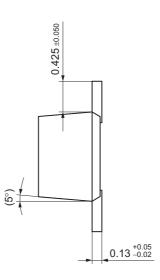




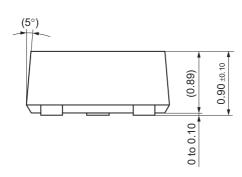
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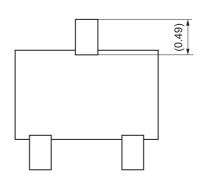
SMini3-F2 Unit: mm











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